

Super Barrier Rectifier TM

Using state-of-the-art SBR IC process technology, the following features are made possible in a single device:

Major ratings and characteristics

Characteristics	Values	Units
$I_{F(AV)}$ Rectangular Waveform	40	А
V _{RRM}	150	V
V _F @20A, Tj=125 ⁰ C	0.73	V, typ
Tj (operating/storage)	-65 to 175	°C

ELECTRICAL:

- * Ultra-Low Forward Voltage Drop
- * Reliable High Temperature Operation
- * Super Barrier Design
- * Softest, fast switching capability
- * 175°C Operating Junction Temperature

Device optimized for low forward voltage drop to maximize efficiency in Power Supply applications

MECHANICAL:

* Molded Plastic TO-220AB, TO-262, TO-263, and ITO-220 packages

Case Styles					
SBR40U150CT	SBR40U150CTF	SBR40U150CTI	SBR40U150CTB		
Anode 1 Common 3 Anode 1 Cathode Anode	Anode Common 3 Anode Anode	Anode Common 3 Anode Anode	2 Common Anode 1 Cathode Anode		
TO-220AB	ITO-220	TO-262	TO-263		



Maximum Ratings and Electrical Cha	racteristics						
(at 25 [°] C unless otherwise specified)							
	SYMBOL			UNITS			
DC Blocking Voltage Working Peak Reverse Voltage Peak Repetitive Reverse Voltage	V _{rm} V _{rwm} V _{rrm}	150		Volts			
Average Rectified Forward Current (Rated V _R -20Khz Square Wave) - 50% duty cycle	Io	40		Amps			
Peak Forward Surge Current - 1/2 60hz	I _{FSM}	300		Amps			
Peak Repetitive Reverse Surge Current (2uS-1Khz)	I _{RRM}	3		Amps			
Instantaneous Forward Voltage (per leg) I _F = 20A; T _J = 25°C I _F = 20A; T _J = 125°C	V _F	Тур 	Max 0.80 0.76	Volts			
Maximum Instantaneous Reverse Current at Rated V_{RM} T _J = 25°C T _J = 125°C	I _R .	Тур 	Max 0.5 25	mA mA			
Maximum Rate of Voltage Change (at Rated V_R)	dv/dt	10,000		V/uS			
Maximum Thermal Resistance JC (per leg) Package = TO-220AB, TO-262, & TO-263 Package = ITO-220	Rθ _{Jc}	2 4		°C/W			
Operating and Storage Junction Temperature	TJ	-65 to +175		°C			

* Pulse width < 300 uS, Duty cycle < 2%

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